



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Description

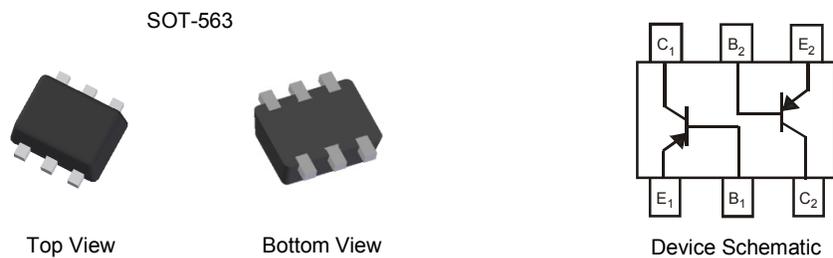
This bipolar junction transistor (BJT) is designed to meet the stringent requirement of automotive applications.

Features

- $BV_{ce0} > -60V$
- $I_C = -600mA$ Collector Current
- Ultra-Small Surface Mount Package

Mechanical Data

- Case: SOT-563
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Plated Leads Solderable per MIL-STD-202, Method 208 
- Weight: 0.003 grams (Approximate)



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit |
|---------------------------|------------------|-------|------|
| Collector-Base Voltage | V _{CB0} | -60 | V |
| Collector-Emitter Voltage | V _{CEO} | -60 | V |
| Emitter-Base Voltage | V _{EBO} | -5 | V |
| Collector Current | I _C | -600 | mA |

Thermal Characteristics

| | | | |
|--|-----------------------------------|-------------|------|
| Total Power Dissipation (Note 5) | P _D | 150 | mW |
| Thermal Resistance, Junction to Ambient (Note 5) | R _{θJA} | 833 | °C/W |
| Operating and Storage Temperature Range | T _J , T _{STG} | -55 to +150 | °C |

ESD Ratings (Note 6)

| Characteristic | Symbol | Value | Unit | JEDEC Class |
|--|---------|-------|------|-------------|
| Electrostatic Discharge - Human Body Model | ESD HBM | 4000 | V | 3A |
| Electrostatic Discharge - Machine Model | ESD MM | 400 | V | C |

- Notes:
- For the device mounted on minimum recommended pad layout FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 - Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information

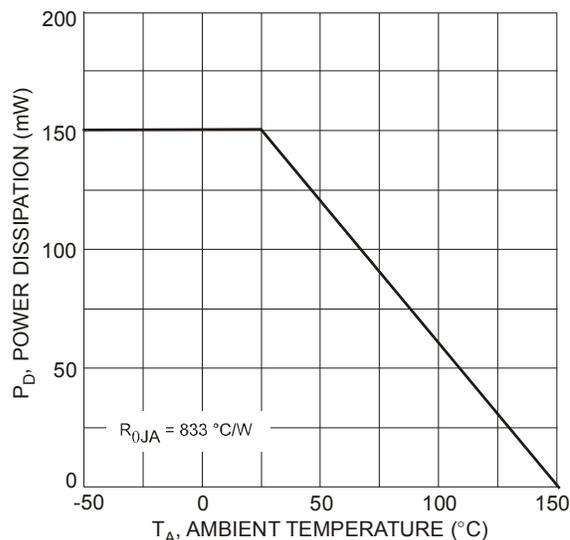


Fig. 1 Power Dissipation vs. Ambient Temperature (Note 3)

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

| Characteristic | Symbol | Min | Max | Unit | Test Condition |
|--|---------------|-------------------------------|-------------------------|---------------------|--|
| OFF CHARACTERISTICS | | | | | |
| Collector-Base Breakdown Voltage | BV_{CBO} | -60 | — | V | $I_C = -10\mu\text{A}, I_E = 0$ |
| Collector-Emitter Breakdown Voltage (Note 7) | BV_{CEO} | -60 | — | V | $I_C = -10\text{mA}, I_B = 0$ |
| Emitter-Base Breakdown Voltage | BV_{EBO} | -5 | — | V | $I_E = -10\mu\text{A}, I_C = 0$ |
| Collector Cut-Off Current | I_{CBO} | — | -10 | nA μA | $V_{CB} = -50\text{V}, I_E = 0$ $V_{CB} = -50\text{V}, I_E = 0, T_A = +125^\circ\text{C}$ |
| Collector Cut-Off Current | I_{CEX} | — | -50 | nA | $V_{CE} = -30\text{V}, V_{EB(OFF)} = -0.5\text{V}$ |
| Base Cut-Off Current | I_{BL} | — | -50 | nA | $V_{CE} = -30\text{V}, V_{EB(OFF)} = -0.5\text{V}$ |
| ON CHARACTERISTICS | | | | | |
| DC Current Gain (Note 7) | h_{FE} | 75 100 100 100 50 | — — — 300 — | — | $I_C = -100\mu\text{A}, V_{CE} = -10\text{V}$ $I_C = -1.0\text{mA}, V_{CE} = -10\text{V}$ $I_C = -10\text{mA}, V_{CE} = -10\text{V}$ $I_C = -150\text{mA}, V_{CE} = -10\text{V}$ $I_C = -500\text{mA}, V_{CE} = -10\text{V}$ |
| Collector-Emitter Saturation Voltage (Note 7) | $V_{CE(sat)}$ | — | -0.4 -1.6 | V | $I_C = -150\text{mA}, I_B = -15\text{mA}$ $I_C = -500\text{mA}, I_B = -50\text{mA}$ |
| Base-Emitter Saturation Voltage (Note 7) | $V_{BE(sat)}$ | — | -1.3 -2.6 | V | $I_C = -150\text{mA}, I_B = -15\text{mA}$ $I_C = -500\text{mA}, I_B = -50\text{mA}$ |
| SMALL SIGNAL CHARACTERISTICS | | | | | |
| Output Capacitance | C_{obo} | — | 8.0 | pF | $V_{CB} = -10\text{V}, f = 1\text{MHz}, I_E = 0$ |
| Input Capacitance | C_{ibo} | — | 30 | pF | $V_{EB} = -2\text{V}, f = 1\text{MHz}, I_C = 0$ |
| Current Gain-Bandwidth Product | f_T | 200 | — | MHz | $V_{CE} = -20\text{V}, I_C = -50\text{mA}, f = 100\text{MHz}$ |
| SWITCHING CHARACTERISTICS | | | | | |
| Turn-On Time | t_{off} | — | 45 | ns | $V_{CC} = -30\text{V}, I_C = -150\text{mA}, I_{B1} = -15\text{mA}$ |
| Delay Time | t_d | — | 10 | ns | |
| Rise Time | t_r | — | 40 | ns | |
| Turn-Off Time | t_{off} | — | 100 | ns | $V_{CC} = -6\text{V}, I_C = -150\text{mA}, I_{B1} = I_{B2} = -15\text{mA}$ |
| Storage Time | t_s | — | 80 | ns | |
| Fall Time | t_f | — | 30 | ns | |

Note: 7. Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$.

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

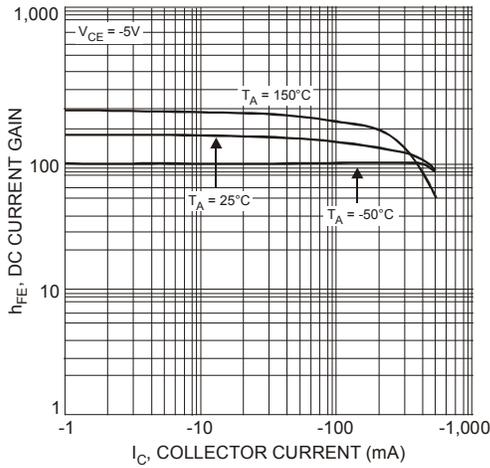


Fig. 2 Typical DC Current Gain vs. Collector Current

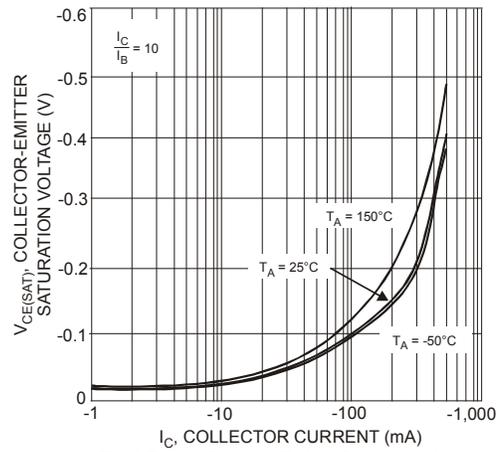


Fig. 3 Typical Collector-Emitter Saturation Voltage vs. Collector Current

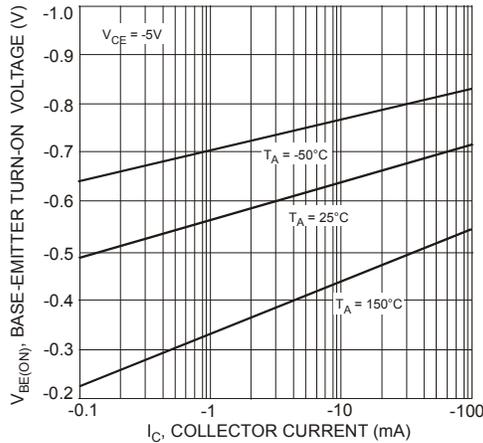


Fig. 4 Typical Base-Emitter Turn-On Voltage vs. Collector Current

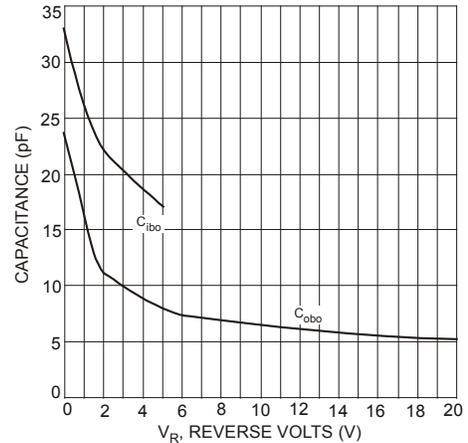


Fig. 5 Typical Capacitance Characteristics

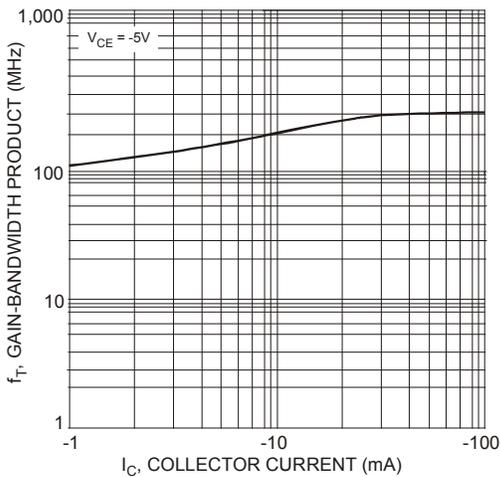


Fig. 6 Typical Gain-Bandwidth Product vs. Collector Current

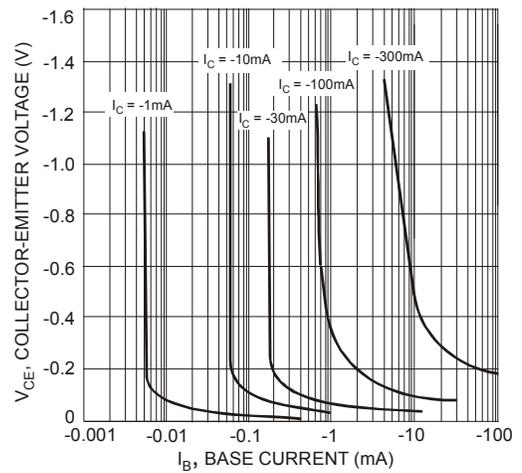
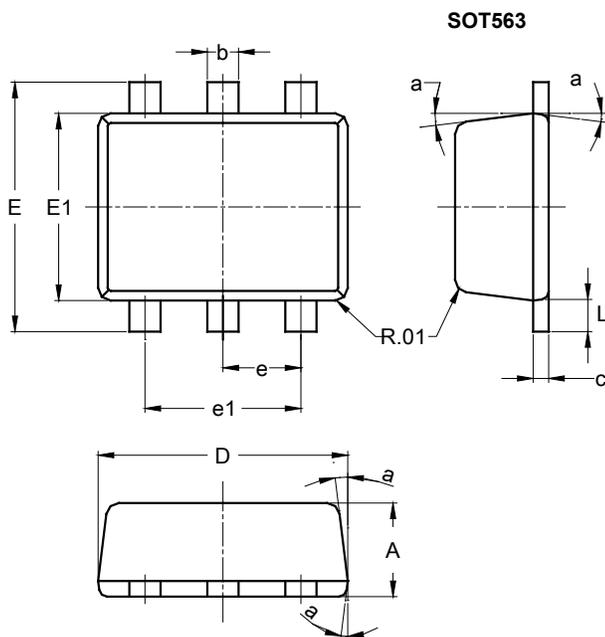


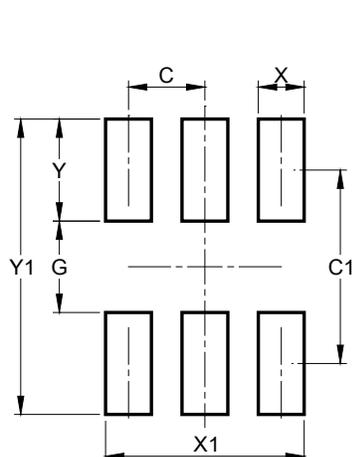
Fig. 7 Typical Collector Saturation Region

Package Outline Dimensions



| SOT563 | | | |
|----------------------|------|------|------|
| Dim | Min | Max | Typ |
| A | 0.55 | 0.60 | 0.60 |
| b | 0.15 | 0.30 | 0.20 |
| c | 0.10 | 0.18 | 0.11 |
| D | 1.50 | 1.70 | 1.60 |
| E | 1.55 | 1.70 | 1.60 |
| E1 | 1.10 | 1.25 | 1.20 |
| e | -- | -- | 0.50 |
| e1 | 0.90 | 1.10 | 1.00 |
| L | 0.10 | 0.30 | 0.20 |
| a | 8° | 9° | 7° |
| All Dimensions in mm | | | |

Suggested Pad Layout



| Dimensions | Value (in mm) |
|------------|---------------|
| C | 0.500 |
| C1 | 1.270 |
| G | 0.600 |
| X | 0.300 |
| X1 | 1.300 |
| Y | 0.670 |
| Y1 | 1.940 |